

RT2A00AM1

COMPOSITE TRANSISTOR
FOR LOW FREQUENCY AMPLIFY APPLICATION
SILICON PNP EPITAXIAL TYPE

ELECTRICAL CHARACTERISTICS (Ta=25°C) (Tr1, Tr2)

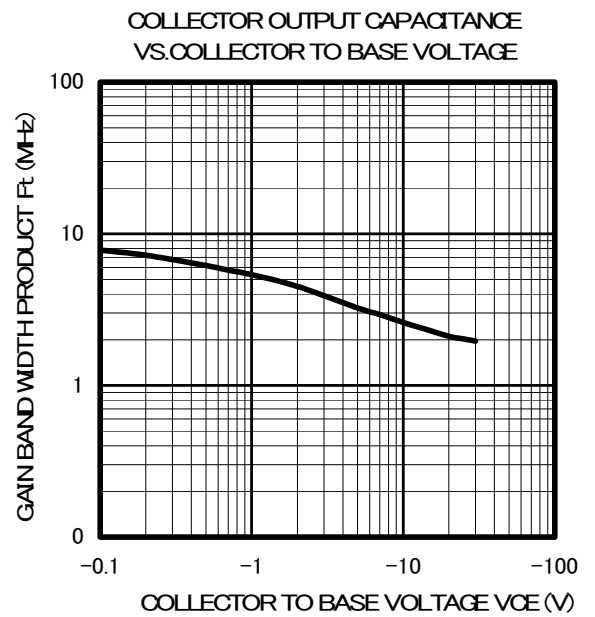
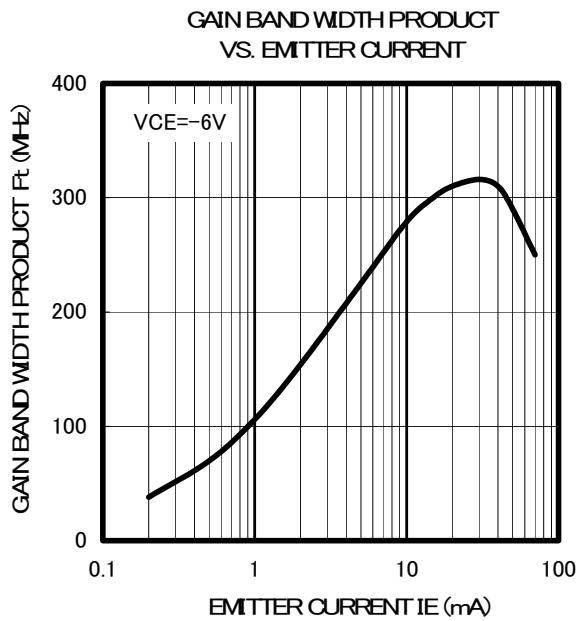
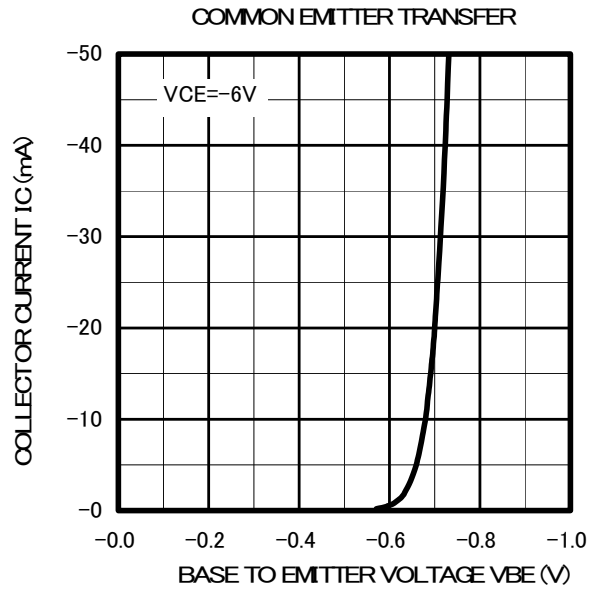
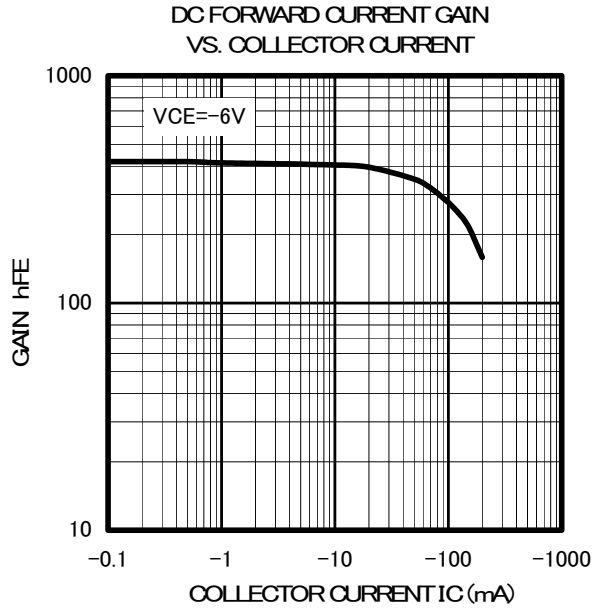
Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CEO}$	Collector to Emitter break down voltage	$I_C = -100 \mu A, R_{BE} = \infty$	-50			V
I_{CBO}	Collector cut off current	$V_{CB} = -60V, I_E = 0mA$			-0.1	μA
I_{EBO}	Emitter cut off current	$V_{EB} = -6V, I_C = 0mA$			-0.1	μA
h_{FE}^*	DC forward current gain	$V_{CE} = -6V, I_C = -1mA$	150		500	-
h_{FE}	DC forward current gain	$V_{CE} = -6V, I_C = -0.1mA$	90			-
$V_{CE(sat)}$	Collector to Emitter saturation voltage	$I_C = -100mA, I_B = -10mA$			-0.3	V
f_T	Gain band width product	$V_{CE} = -6V, I_E = 10mA$		200		MHz
Cob	Collector output capacitance	$V_{CB} = -6V, I_E = 0mA, f = 1MHz$		4.0		pF
NF	Noise figure	$V_{CE} = -6V, I_E = 0.3mA, f = 100Hz, R_G = 10k\Omega$			20	dB

* : It shows h_{FE} classification in right table.

ITEM	E	F
h_{FE}	150~300	250~500
MARKING	·ME	·MF

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